



STC04IE170HV

Monolithic emitter switched bipolar transistor
ESBT® 1700 V - 4 A - 0.17 Ω

Features

$V_{CS(ON)}$	I_C	$R_{CS(ON)}$
0.7 V	4 A	0.17 Ω

- High voltage / high current cascode configuration
- Low equivalent ON resistance
- Very fast-switch: up to 150 kHz
- Squared RBSOA: up to 1700 V
- Very low C_{ISS} driven by $R_G = 47 \Omega$
- Very low turn-off cross over time

Application

- Aux SMPS for three-phase mains

Description

The STC04IE170HV is manufactured in monolithic ESBT technology, aimed at providing the best performance in high frequency / high voltage applications. It is designed for use in gate driven based topologies.

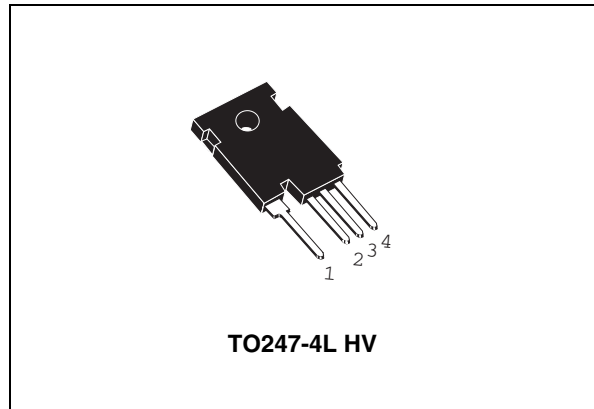


Figure 1. Internal schematic diagrams

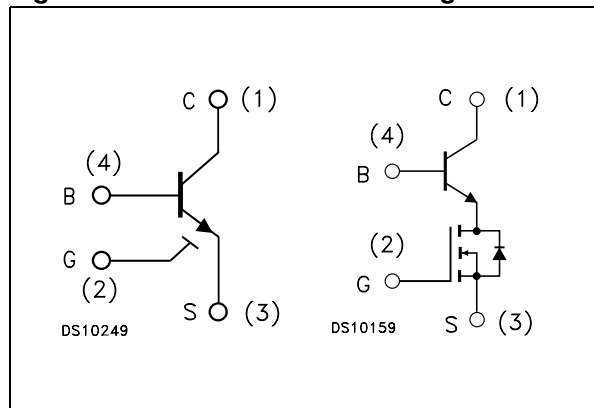


Table 1. Device summary

Order code	Marking	Package	Packing
STC04IE170HV	C04IE170HV	TO247-4L HV	Tube

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
$V_{CS(SS)}$	Collector-source voltage ($V_{BS} = V_{GS} = 0$)	1700	V
$V_{BS(OS)}$	Base-source voltage ($I_C = 0, V_{GS} = 0$)	30	V
$V_{SB(OS)}$	Source-base voltage ($I_C = 0, V_{GS} = 0$)	17	V
V_{GS}	Gate-source voltage	± 17	V
I_C	Collector current	4	A
I_{CM}	Collector peak current ($t_P < 5$ ms)	8	A
I_B	Base current	4	A
I_{BM}	Base peak current ($t_P < 1$ ms)	8	A
P_{tot}	Total dissipation at $T_c \leq 25$ °C	178	W
T_{stg}	Storage temperature	-40 to 150	°C
T_J	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case	0.7	°C/W

2 Electrical characteristics

($T_{case} = 25\text{ °C}$ unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{CS(SS)}$	Collector cut-off current ($V_{BS} = V_{GS} = 0$)	$V_{CS} = 1700\text{ V}$			100	μA
$I_{BS(OS)}$	Base cut-off current ($I_C = 0, V_{GS} = 0$)	$V_{BS} = 30\text{ V}$			10	μA
$I_{SB(OS)}$	Source cut-off current ($I_C = 0, V_{GS} = 0$)	$V_{SB} = 17\text{ V}$			100	μA
$I_{GS(OS)}$	Gate-source leakage current ($V_{BS} = 0$)	$V_{GS} = \pm 17\text{ V}$			100	nA
$V_{CS(ON)}$	Collector-source ON voltage	$V_{GS} = 10\text{ V } I_C = 4\text{ A } I_B = 0.8\text{ A}$ $V_{GS} = 10\text{ V } I_C = 1.5\text{ A } I_B = 0.15\text{ A}$		0.7 0.6	1.5 1.4	V V
$h_{FE}^{(1)}$	DC current gain	$V_{CS} = 1\text{ V } V_{GS} = 10\text{ V } I_C = 4\text{ A}$ $V_{CS} = 1\text{ V } V_{GS} = 10\text{ V } I_C = 1.5\text{ A}$	4 7	5.5 11		
$V_{BS(ON)}$	Base-source ON voltage	$V_{GS} = 10\text{ V } I_C = 4\text{ A } I_B = 0.8\text{ A}$ $V_{GS} = 10\text{ V } I_C = 1.5\text{ A } I_B = 0.15\text{ A}$		1.3 0.9	1.5 1.1	V V
$V_{GS(th)}$	Gate threshold voltage	$V_{BS} = V_{GS} I_B = 250\text{ }\mu\text{A}$	2	3	4	V
C_{iss}	Input capacitance ($V_{GS} = V_{CB} = 0$)	$V_{CS} = 25\text{ V } f = 1\text{ MHz}$		510		pF
$Q_{GS(tot)}$	Gate-source charge ($V_{CB} = 0$)	$V_{GS} = 10\text{ V}$		3.9		nC
t_s t_f	Inductive load Storage time Fall time	$V_{GS} = 10\text{ V } R_G = 47\text{ }\Omega$ $V_{Clamp} = 1360\text{ V } t_p = 4\text{ }\mu\text{s}$ $I_C = 2\text{ A } I_B = 0.4\text{ A}$		770 10		ns ns
t_s t_f	Inductive load Storage time Fall time	$V_{GS} = 10\text{ V } R_G = 47\text{ }\Omega$ $V_{Clamp} = 1360\text{ V } t_p = 4\text{ }\mu\text{s}$ $I_C = 2\text{ A } I_B = 0.2\text{ A}$		410 10		ns ns
$V_{CS(dyn)}$	Collector-source dynamic voltage (0.5 μs)	$V_{CC} = V_{Clamp} = 400\text{ V}$ $V_{GS} = 10\text{ V } I_C = 1.5\text{ A}$ $I_B = 0.3\text{ A } t_{peak} = 500\text{ ns}$ $R_G = 47\text{ }\Omega I_{Bpeak} = 3\text{ A } (2I_C)$		5.36		V
$V_{CS(dyn)}$	Collector-source dynamic voltage (1 μs)	$V_{CC} = V_{Clamp} = 400\text{ V}$ $V_{GS} = 10\text{ V } I_C = 1.5\text{ A}$ $I_B = 0.3\text{ A } t_{peak} = 500\text{ ns}$ $R_G = 47\text{ }\Omega I_{Bpeak} = 3\text{ A } (2I_C)$		4.32		V
V_{CSW}	Maximum collector- source voltage at turn- off without snubber	$R_G = 47\text{ }\Omega h_{FE} = 5 I_C = 4\text{ A}$	1700			V

1. Pulsed duration = 300 μs , duty cycle $\leq 1.5\%$.

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

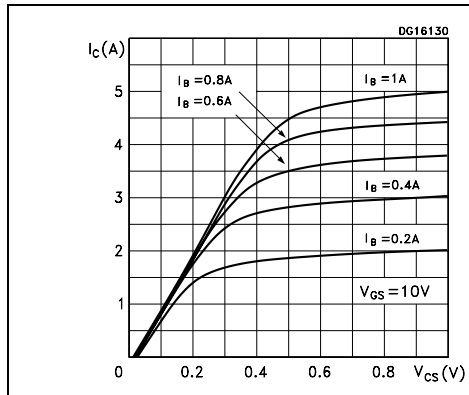


Figure 3. Collector-source dynamic voltage

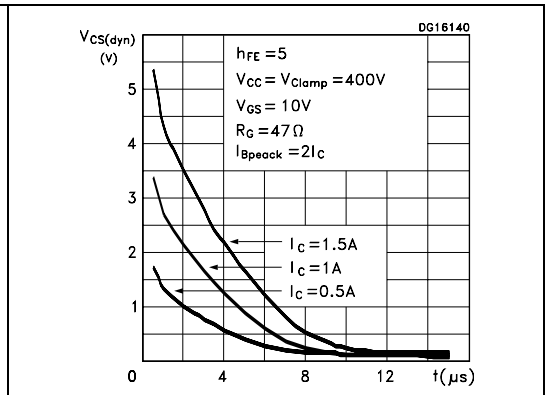


Figure 4. DC current gain

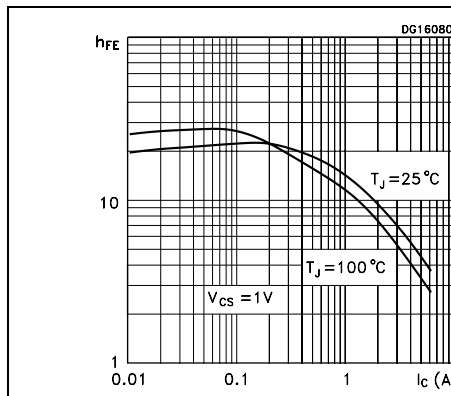


Figure 5. Gate threshold voltage vs. temperature

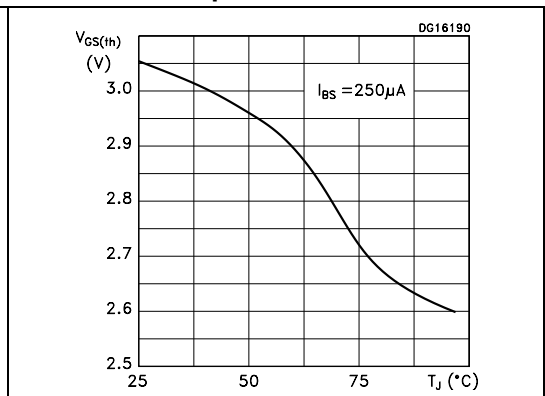


Figure 6. Collector-source ON voltage ($h_{FE} = 5$)

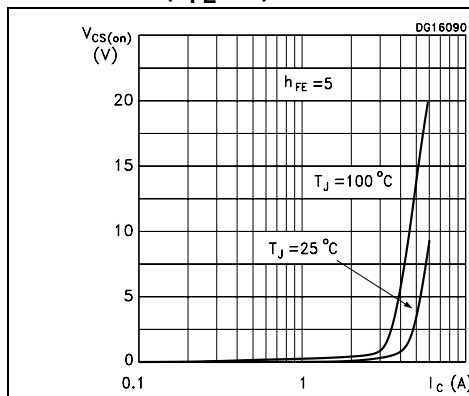


Figure 7. Collector-source ON voltage ($h_{FE} = 10$)

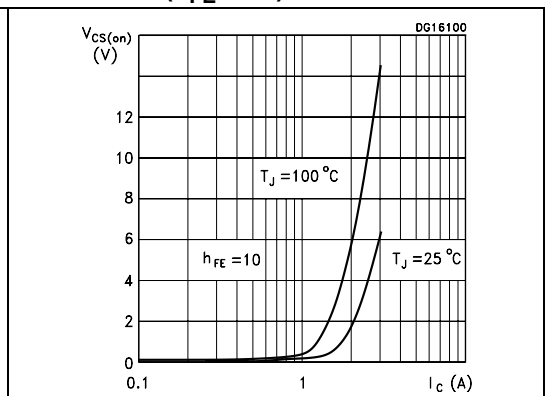


Figure 8. Base-source ON voltage ($h_{FE} = 5$)

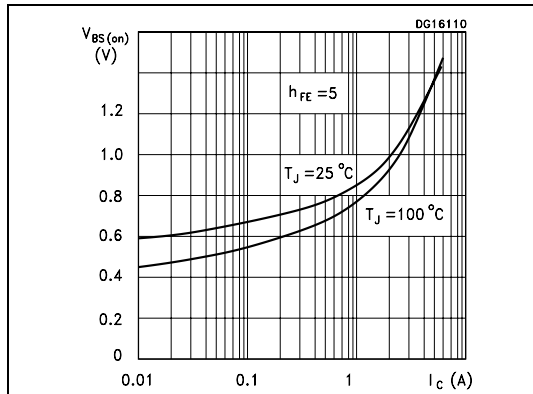


Figure 9. Base-source ON voltage ($h_{FE} = 10$)

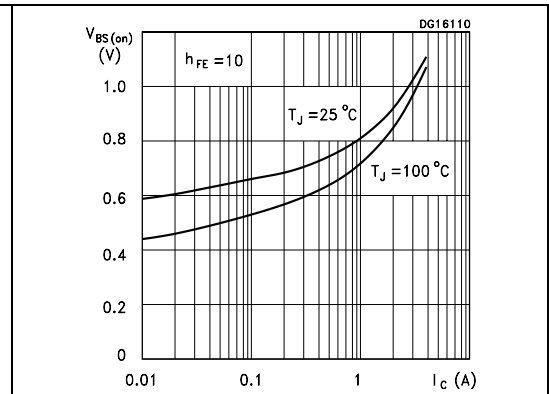


Figure 10. Inductive load switching time ($h_{FE} = 5$)

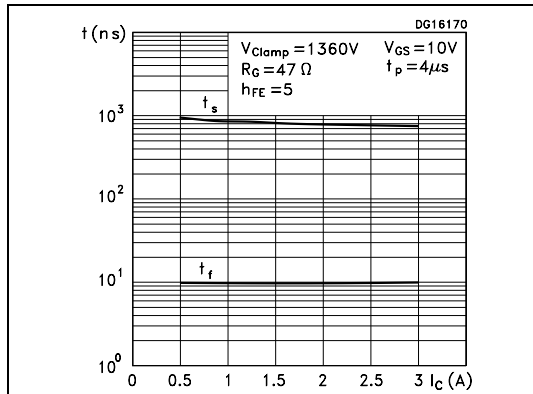


Figure 11. Inductive load switching time ($h_{FE} = 10$)

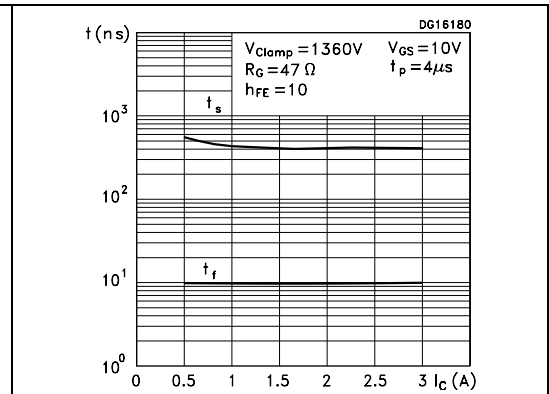
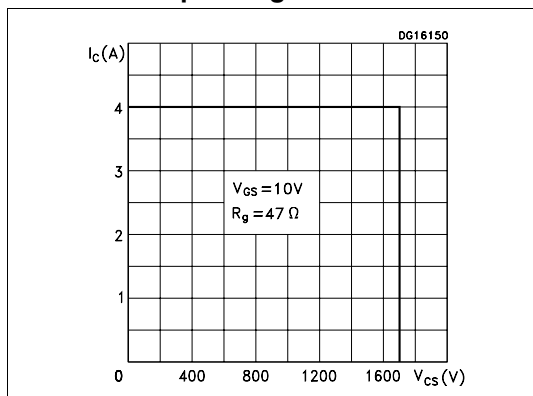


Figure 12. Reverse biased safe operating area

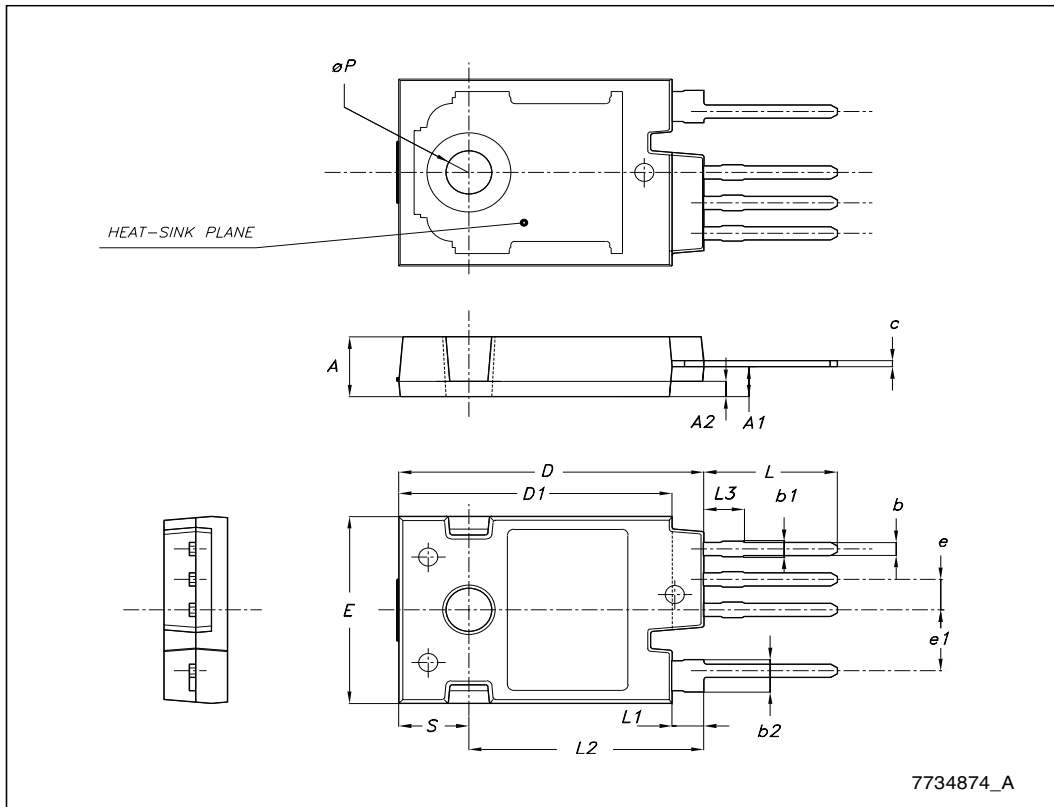


3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

TO247-4L HV mechanical data

DIM.	mm.		
	MIN.	TYP	MAX.
A	4.85		5.15
A1	2.20	2.50	2.60
A2		1.27	
b	0.95	1.10	1.30
b1	1.10		1.50
b2	2.50		2.90
c	0.40		0.80
D	23.85	24	24.15
D1		21.50	
E	15.45	15.60	15.75
e		2.54	
e1		5.08	
L	10.20		10.80
L1	2.20	2.50	2.80
L2		18.50	
L3		3	
øP	3.55		3.65
S		5.50	



4 Revision history

Table 5. Document revision history

Date	Revision	Changes
11-Sep-2006	1	First release.
21-Nov-2006	2	Improved application target.
16-Jun-2009	3	Updated Figure 2 on page 4 and mechanical data.

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